New Jersey Semi-Conductor Products, Inc.

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2N4302

N–Channel JFET Silicon Transistor General Purpose AF Amplifier

<u>Absolute Maximum Ratings:</u> ($T_A = +25^{\circ}C$ unless otherwise specified)

Drain–Source Voltage, V _{DS}	25V
Drain–Gate Voltage, V _{DG}	25V
Gate-Source Voltage, V _{GS}	_25 V
Gate Current, I _G	10mA
Total Device Dissipation (T _A = +25°C), P _D Derate Above 25°C	300mW 2mW/°C
Operating Junction Temperature Range, T _J	–55° to +150°C
Storage Temperature Range, T _{stg}	–55° to +150°C
Lead Temperature (During Soldering, 1/16" from case for 10sec), T _L	+260°C

Electrical Characteristics: ($T_A = +25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Gate-Source Breakdown Voltage	V _{(BR)GSS}	$I_{G} = 1\mu A, V_{DS} = 0$	-25	-	-	V
Gate Reverse Current	I _{GSS}	V _{GS} = 20V, V _{DS} = 0	-	-	-1	nA
		V _{GS} = 20V, V _{DS} = 0, T _A = +150°C	-	-	-1	μA
Gate-Source Cutoff Voltage	V _{GS(off)}	I _D = 1μΑ, V _{DS} = 15V	-	-	-6.5	V
Gate-Source Voltage	V _{GS}	I _D = 50μA, V _{DS} = 15V	-0.4	-	-6.0	V
Zero-Gate-Voltage Drain Current	I _{DSS}	V _{DS} = 15V, V _{GS} = 0	0.5	-	15	mA
Forward Transfer Admittance	Y _{fs}	V _{DS} = 15V, V _{GS} = 0, f = 1kHz	1000	-	7500	μmho



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

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